2SK2016

Silicon N-Channel Power F-MOS

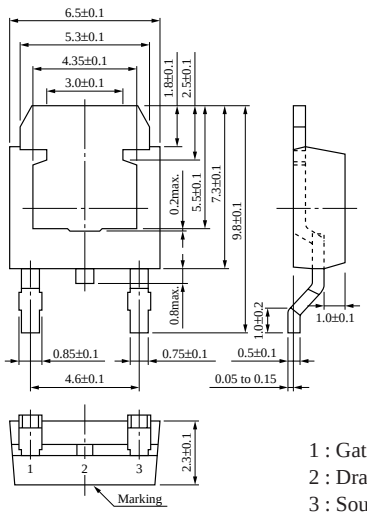
■ Features

- Low ON-resistance $R_{DS(on)}$: $R_{DS(on)}1$= 0.315Ω(typ)
- High-speed switching : t_f= 38ns(typ)
- No secondary breakdown
- For low-voltage drive(V_{GS}= 4V)
- Taping supply possible

■ Applications

- DC-DC converter
- Non-contact relay
- Solenoid drive
- Motor drive

Unit : mm



1 : Gate
2 : Drain
3 : Source
EIAJ : SC-63
U Type Package

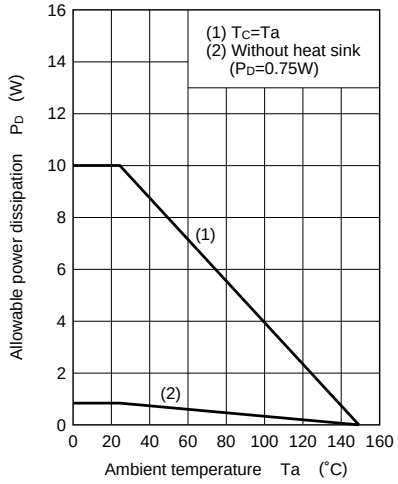
■ Absolute Maximum Ratings (Tc = 25˚C)

Parameter		Symbol	Rating	Unit
Drain-Source breakdown voltage		V_{DSS}	100	V
Gate-Source voltage		V_{GSS}	±20	V
Drain current	at 4V drive	I_D	±3	A
	DC		±5	
	Pulse	I_{DP}	±10	A
Allowable power dissipation	T_C= 25˚C	P_D	10	W
	Ta=25˚C		0.75	
Channel temperature		T_{ch}	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

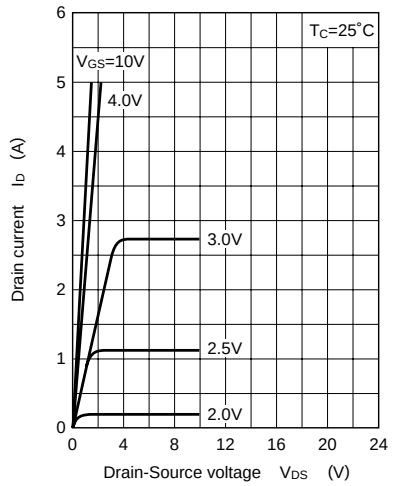
■ Electrical Characteristics (Tc = 25˚C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	V_{DS}= 80V, V_{GS}= 0			10	μ A
Gate-Source leakage current	I_{GSS}	V_{GS}= ±20V, V_{DS}= 0			±1	μ A
Drain-Source breakdown voltage	V_{DSS}	I_D=1mA, V_{GS}= 0	100			V
Gate threshold voltage	V_{th}	V_{DS}=10V, I_D=1mA	1		2.5	V
Drain-Source ON-resistance	$R_{DS(on)}$ 1	V_{GS}=10V, I_D= 3A		0.315	0.47	Ω
	$R_{DS(on)}$ 2	V_{GS}= 4V, I_D= 2A		0.4	0.6	Ω
Forward transadmittance	$\|Y_{fs}\|$	V_{DS}=10V, I_D= 3A	2.5	3.8		S
Input capacitance	C_{iss}	V_{DS}=10V, V_{GS}= 0, f= 1MHz		416		pF
Output capacitance	C_{oss}			135		pF
Feedback capacitance	C_{rss}			38		pF
Turn-on time	t_{on}	V_{GS}=10V, I_D= 3A V_{DD}= 30V, R_L=10Ω		26		ns
Fall time	t_f			38		ns
Turn-off time (delay time)	$t_{d(off)}$			84		ns

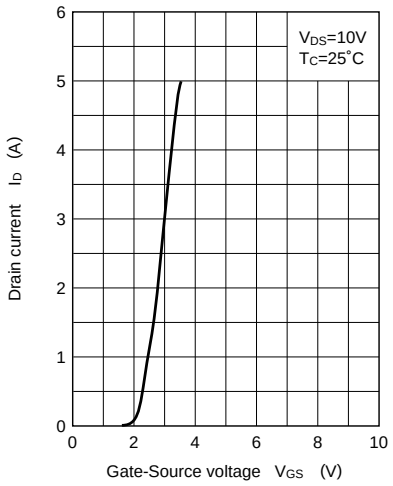
$P_D - Ta$



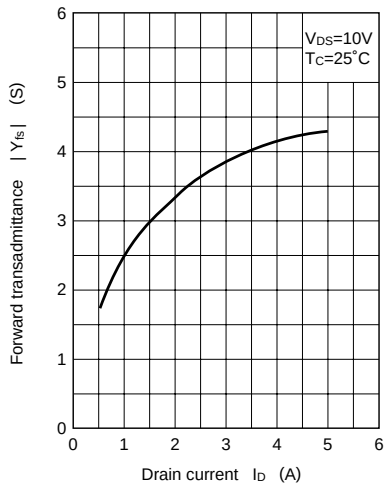
$I_D - V_{DS}$



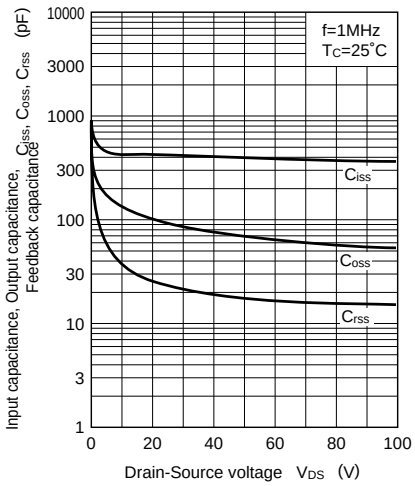
$I_D - V_{GS}$



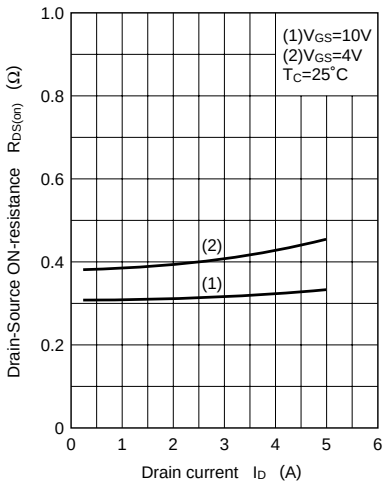
$|Y_{fs}| - I_D$



$C_{iss}, C_{oss}, C_{rss} - V_{DS}$



$R_{DS(on)} - I_D$



$t_{on}, t_f, t_{d(off)} - I_D$